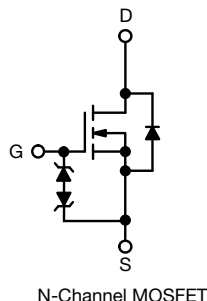


# E Series Power MOSFET

## Thin-Lead TO-220 FULLPAK



## FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low effective capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Integrated Zener diode ESD protection
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy

## PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	850	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	1.17
$Q_g$ max. (nC)	16.5	
$Q_{gs}$ (nC)	3	
$Q_{gd}$ (nC)	6	
Configuration	Single	

## ORDERING INFORMATION

Package	Thin-Lead TO-220 FULLPAK
Lead (Pb)-free and halogen-free	SiHA5N80AE-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	800	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C) <sup>e</sup>	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	7	
Linear derating factor		0.5	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	17	mJ
Maximum power dissipation	$P_D$	29	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dv/dt$	70	V/ns
Reverse diode $dv/dt$ <sup>d</sup>		0.3	
Soldering recommendations (peak temperature) <sup>c</sup>	For 10 s	260	°C
Mounting torque, M3 screw		0.6	Nm


### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 1.1$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ ,  $di/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C
- Limited by maximum junction temperature

**THERMAL RESISTANCE RATINGS**

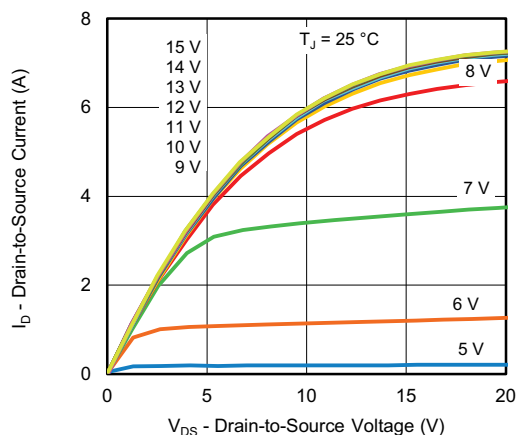
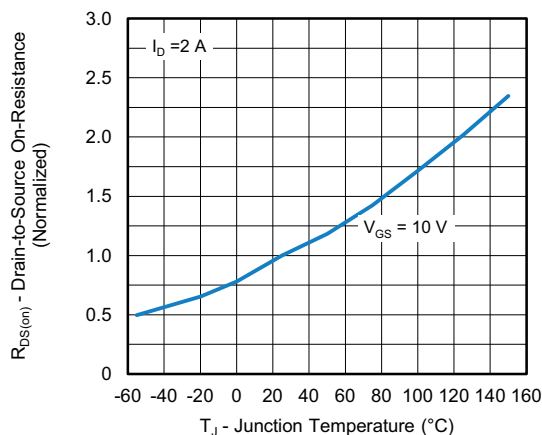
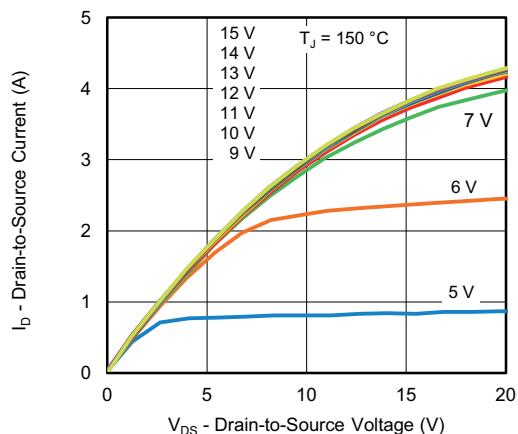
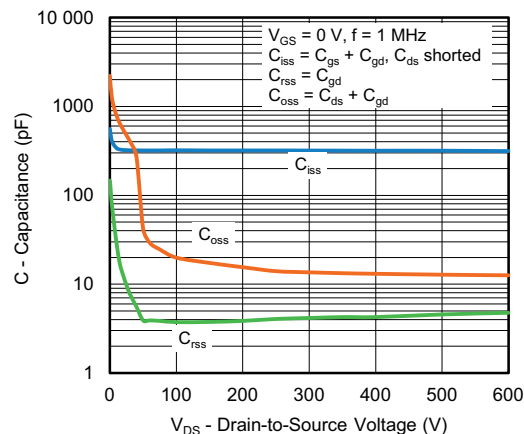
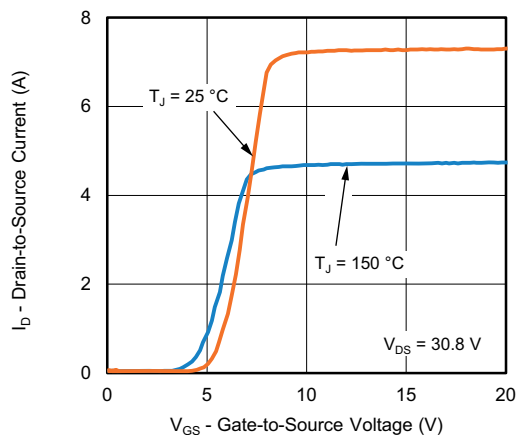
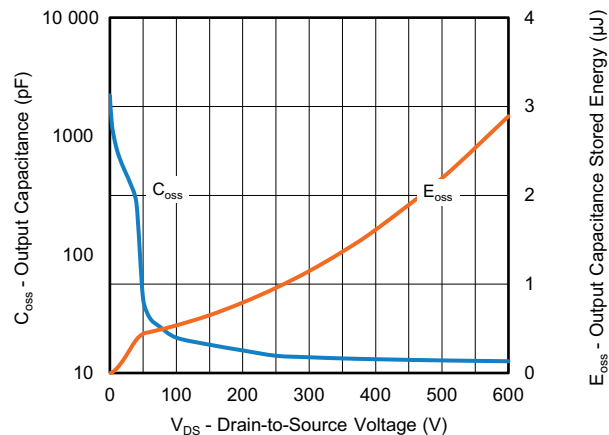
PARAMETER	SYMBOL	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	65	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	4.3	

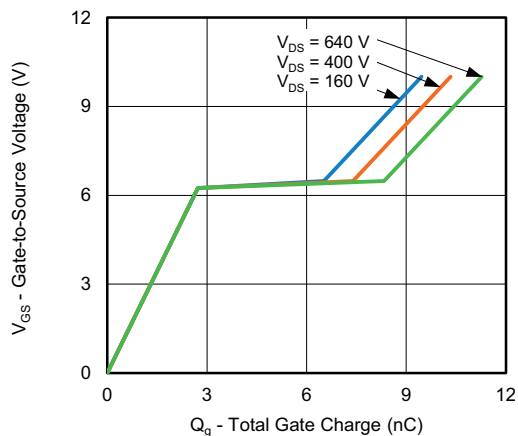
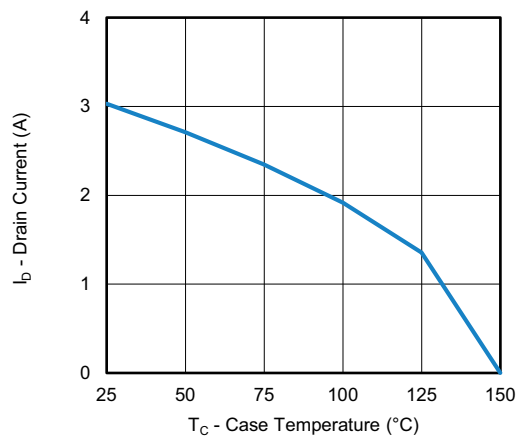
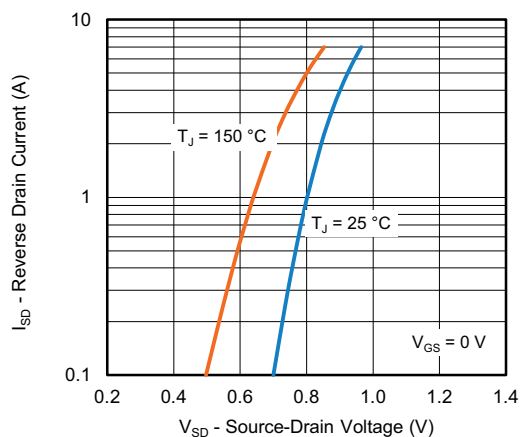
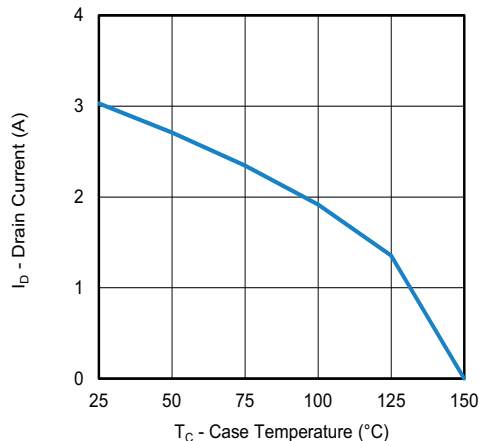
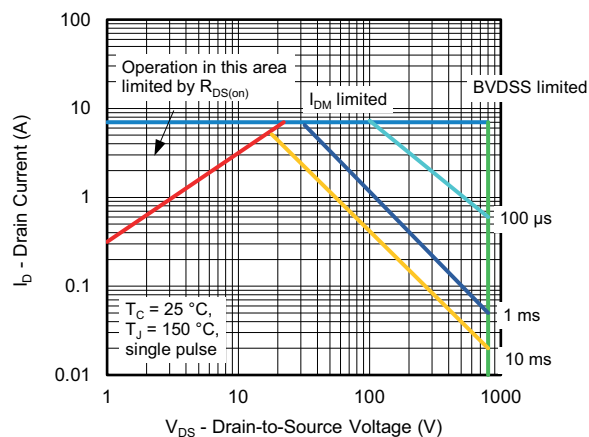
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	800	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 1\text{ mA}$	-	0.8	-	V/ $^{\circ}\text{C}$
Gate-source threshold voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	-	4	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 10$	$\mu\text{A}$
		$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 50$	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 640\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$	-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 1.5\text{ A}$	-	1.17	1.35	$\Omega$
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 30\text{ V}$ , $I_D = 2\text{ A}$	-	1.2	-	S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$	-	321	-	$\text{pF}$
Output capacitance	$C_{oss}$		-	20	-	
Reverse transfer capacitance	$C_{rss}$		-	4	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	14	-	$\text{pF}$
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$		-	71	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}$ , $I_D = 2\text{ A}$ , $V_{DS} = 640\text{ V}$	-	11	16.5	$\text{nC}$
Gate-source charge	$Q_{gs}$		-	3	-	
Gate-drain charge	$Q_{gd}$		-	6	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 640\text{ V}$ , $I_D = 2\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$	-	12	24	$\text{ns}$
Rise time	$t_r$		-	8	16	
Turn-off delay time	$t_{d(off)}$		-	10	20	
Fall time	$t_f$		-	28	56	
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	1.6	3.2	6.4	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	4.4	A
Pulsed diode forward current	$I_{SM}$		-	-	7	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 2\text{ A}$ , $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S = 2\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 25\text{ V}$	-	267	534	ns
Reverse recovery charge	$Q_{rr}$		-	1.2	2.4	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$		-	7.5	-	A

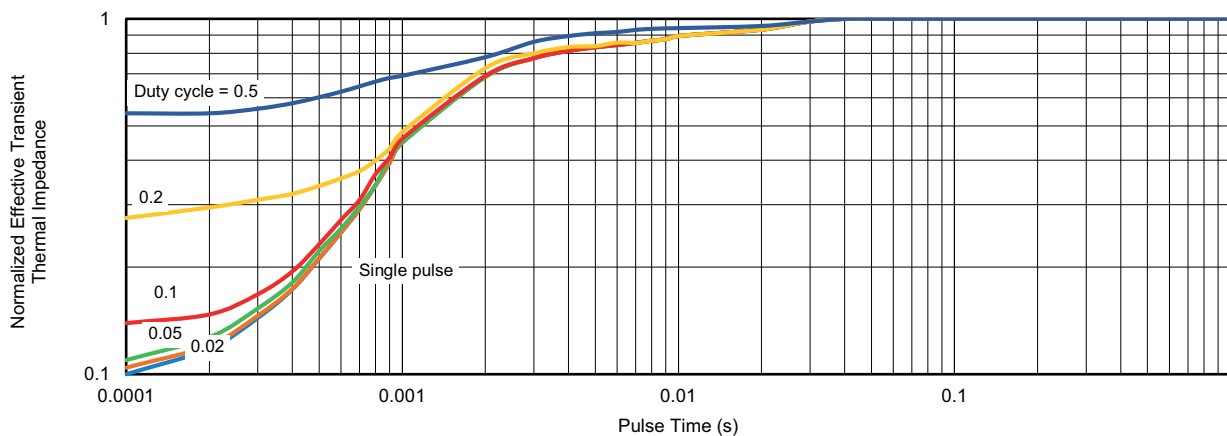
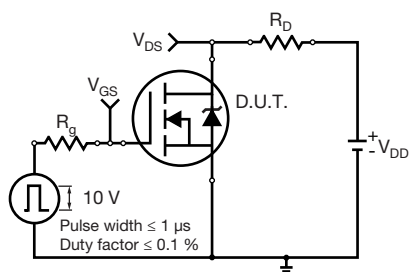
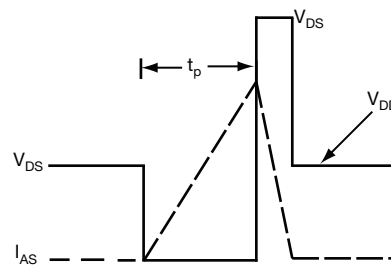
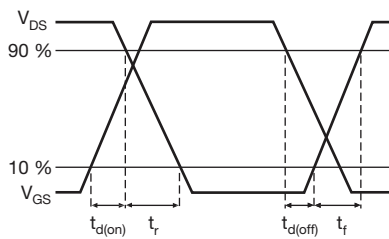
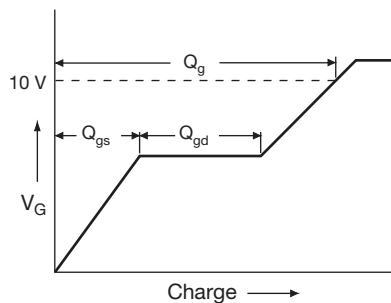
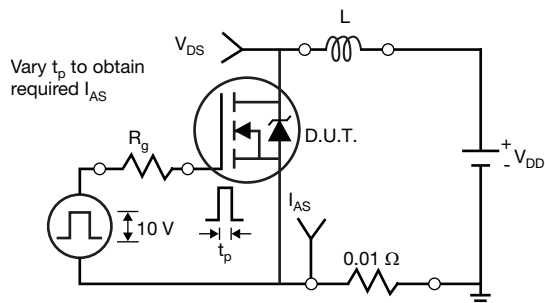
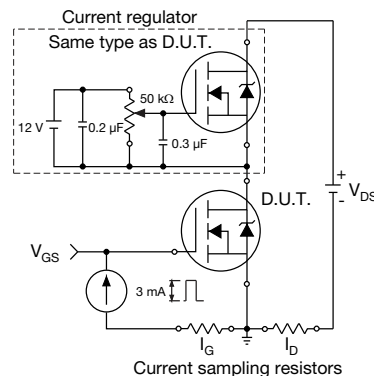
**Notes**

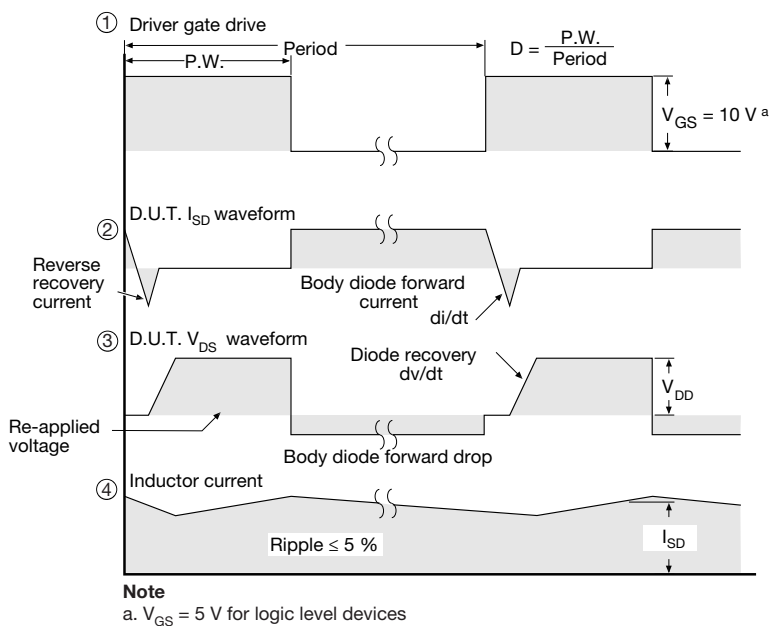
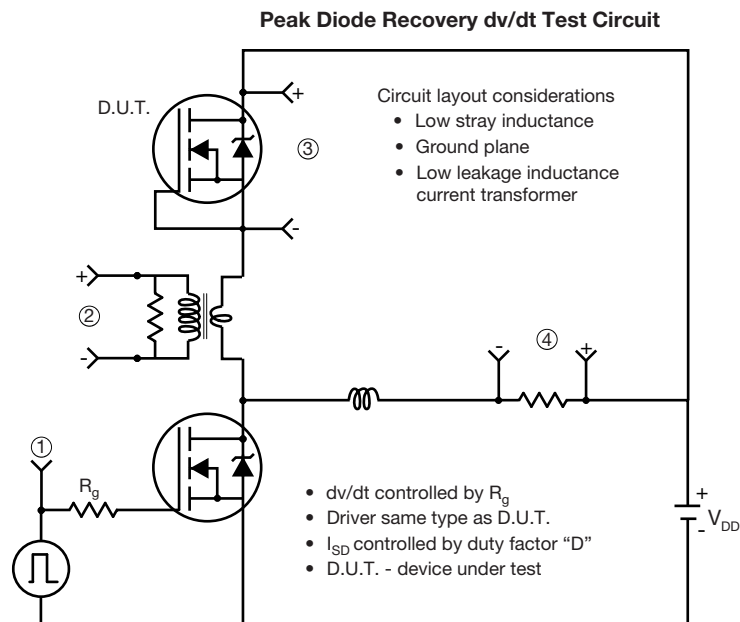
- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 480 V  $V_{DSS}$   
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 480 V  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Normalized Breakdown Voltage vs. Temperature**

**Fig. 9 - Maximum Safe Operating Area**
**Note**

- a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified


**Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case**

**Fig. 13 - Switching Time Test Circuit**

**Fig. 16 - Unclamped Inductive Waveforms**

**Fig. 14 - Switching Time Waveforms**

**Fig. 17 - Basic Gate Charge Waveform**

**Fig. 15 - Unclamped Inductive Test Circuit**

**Fig. 18 - Gate Charge Test Circuit**

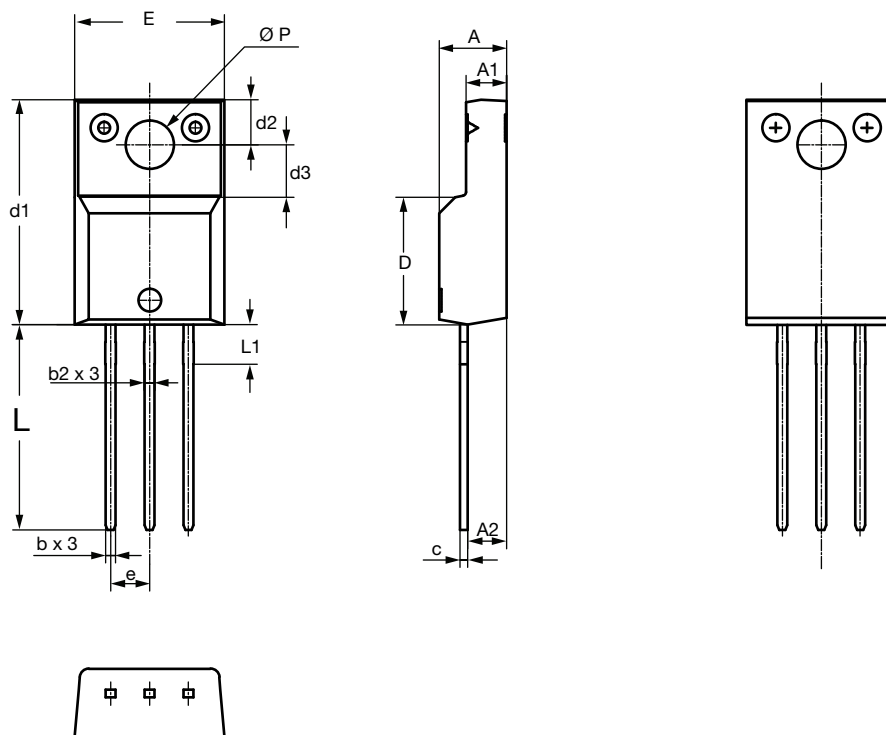


**Fig. 19 - For N-Channel**

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## TO-220 FULLPAK Thin Lead



SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.30	4.70	0.169	0.185
A1	2.50	2.90	0.098	0.114
A2	2.40	2.80	0.094	0.110
b	0.60	0.80	0.024	0.031
b2	0.60	0.90	0.024	0.035
c	-	0.60	-	0.024
D	8.30	8.70	0.327	0.342
d1	14.70	15.30	0.579	0.602
d2	2.90	3.10	0.114	0.122
d3	3.30	3.70	0.130	0.146
E	9.70	10.30	0.382	0.406
e	2.50	2.70	0.098	0.106
L	13.40	13.80	0.528	0.543
L1	1.00	2.80	0.039	0.110
Ø P	3.00	3.40	0.118	0.134
ECN: E20-0684-Rev. D, 28-Dec-2020 DWG: 6021				



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